L Number	Hits	Search Text	DB	Time stamp
-	111	(thin adj film adj transistor$1 tft) with (sensor$3 and switch$3) same capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 11:00
-	6	5895936.URPN.	USPAT	2004/10/29 08:54
-	9	("5003356" | "5032883" | "5313066" | "5319206" | "5352897" | "5396072" | "5463225" | "5498880" | "5563421").PN.	USPAT	2004/10/29 08:54
-	118	(thin adj film adj transistor$1 tft) with (sensor$3 and switch$3) and (memory capacitor) and ohmic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 09:39
-	111	(thin adj film adj transistor$1 tft) with (sensor$3 and switch$3) same capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 09:40
-	80	((thin adj film adj transistor$1 tft) with (sensor$3 and switch$3) and (memory capacitor) and ohmic) not ((thin adj film adj transistor$1 tft) with (sensor$3 and switch$3) same capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 09:40
-	3	(thin adj film adj transistor$1 tft) with (sensor$3 and access$3) same capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 11:01
-	3	(thin adj film adj transistor$1 tft) with (sensor$3 and acces$3) same capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 11:01
-	4	(thin adj film adj transistor$1 tft) with (sensor$3 and access$3) and capacitor not ((thin adj film adj transistor$1 tft) with (sensor$3 and access$3) same capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 11:44
-	2	("5466620").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 11:50
-	2	("5436182").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 11:50
-	4236	(257/59,53,54,57,184,187).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 13:38
-	1819	(tft thin near film near transistor) and ((257/59,53,54,57,184,187).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 13:38

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-	821	((tft thin near film near transistor) and ((257/59,53,54,57,184,187).CCLS.)) and (capacitor memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 13:38
-	587	(tft thin near film near transistor) same switch$3 and (((tft thin near film near transistor) and ((257/59,53,54,57,184,187).CCLS.)) and (capacitor memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 13:39
-	571	(tft thin near film near transistor) with switch$3 and (((tft thin near film near transistor) and ((257/59,53,54,57,184,187).CCLS.)) and (capacitor memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 13:39
-	511	(tft thin near film near transistor) near3 switch$3 and (((tft thin near film near transistor) and ((257/59,53,54,57,184,187).CCLS.)) and (capacitor memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 13:47
-	24	(((tft thin near film near transistor) and ((257/59,53,54,57,184,187).CCLS.)) and (capacitor memory)) and dual near3 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 14:19
-	16	(((tft thin near film near transistor) same (capacitor memory) and ((257/59,53,54,57,184,187).CCLS.))) and dual near3 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 14:24
-	31	(((tft thin near film near transistor) same (capacitor memory) and (438/$6 257/$6))) and dual near3 electrode not ((((tft thin near film near transistor) same (capacitor memory) and ((257/59,53,54,57,184,187).CCLS.))) and dual near3 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 14:30
-	52	(((tft thin near film near transistor) same (capacitor memory) and (438/$6 257/$6))) and dual near4 electrode not ((((tft thin near film near transistor) same (capacitor memory) and ((257/59,53,54,57,184,187).CCLS.))) and dual near3 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 14:34